Pmax =Pm= maximum Power

Isc = Short Circuit Current

Vmax = Vmp= Maximum Power

Voc = Open Circuit VOltage

Voltage

ff = fill factor

Imax = Imp = Maximum Power

eff = Panel Efficiency

Current

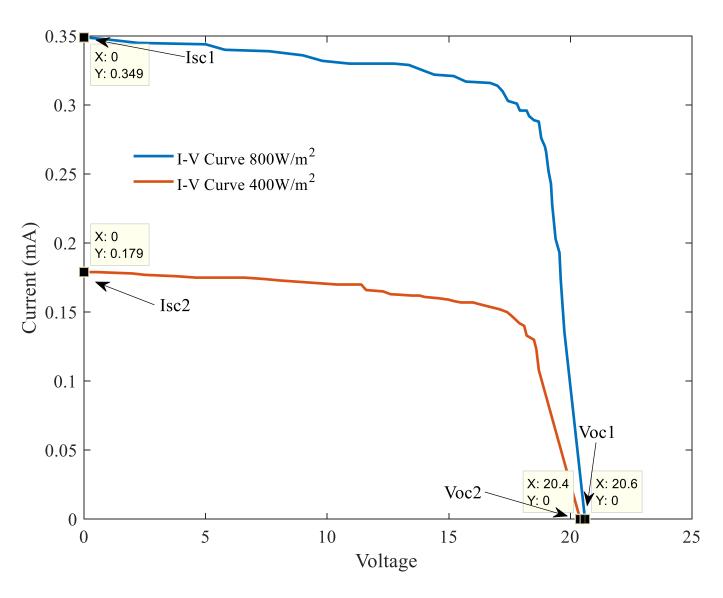
Rsh = Shunt Resistance

Ideality Factor of Silicon Cell =

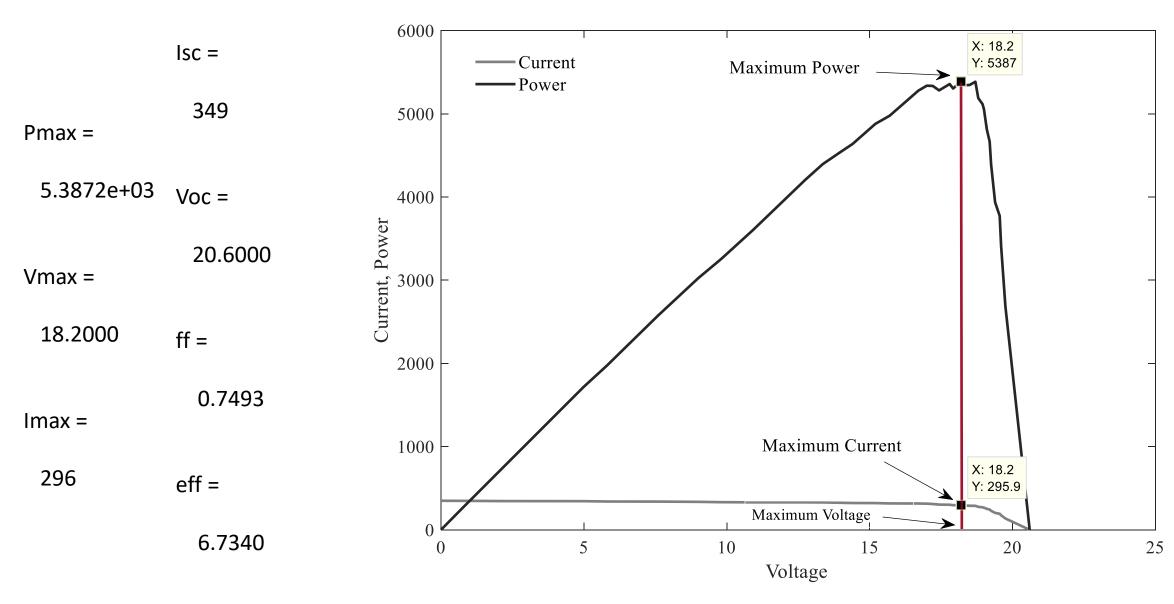
Rs = Series Resistance

1.5

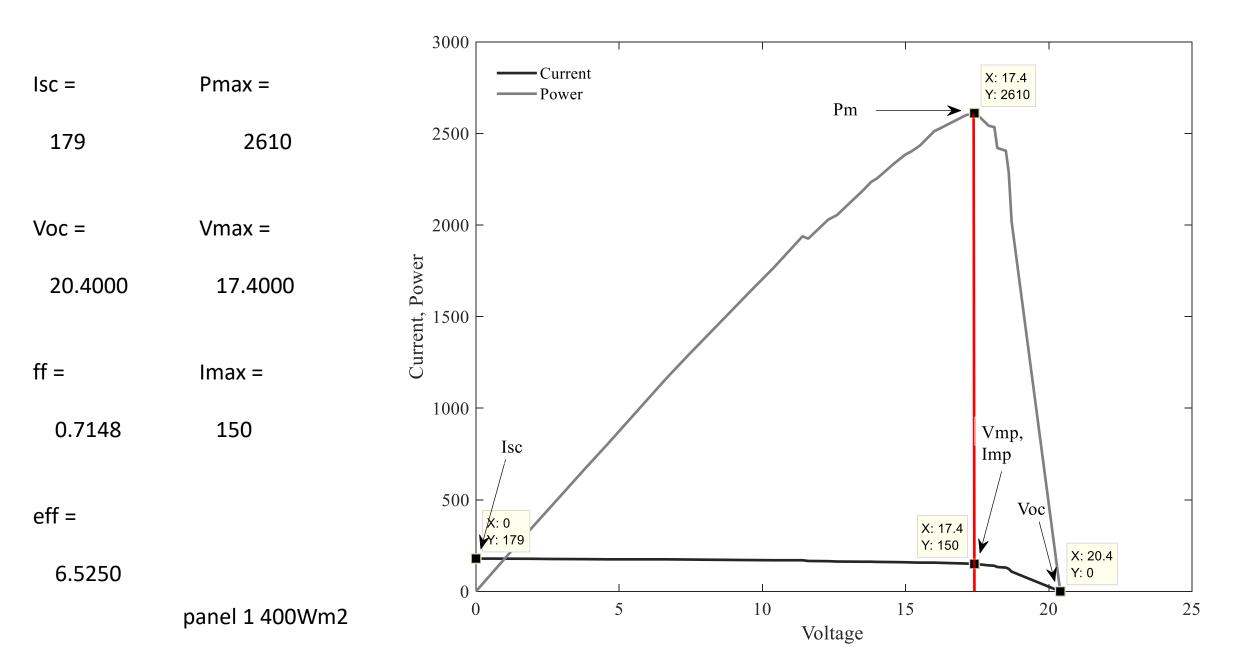
Number of Cells = 36

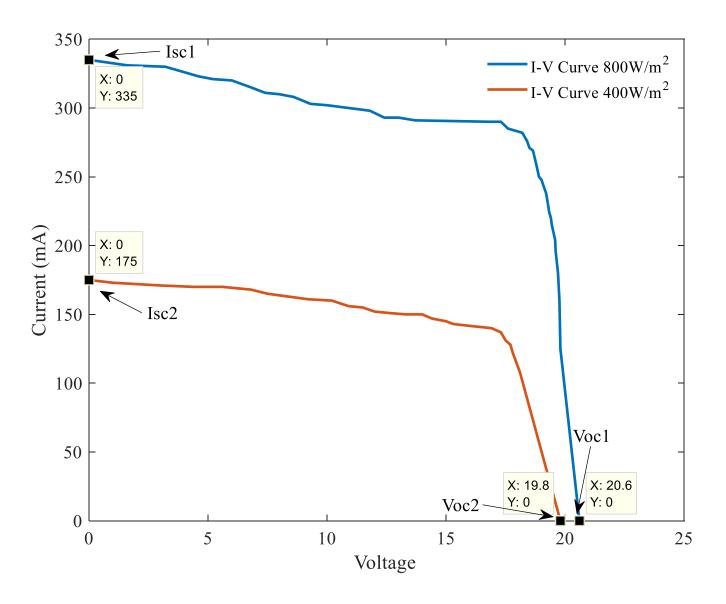


I-V Characteristics of Panel 01

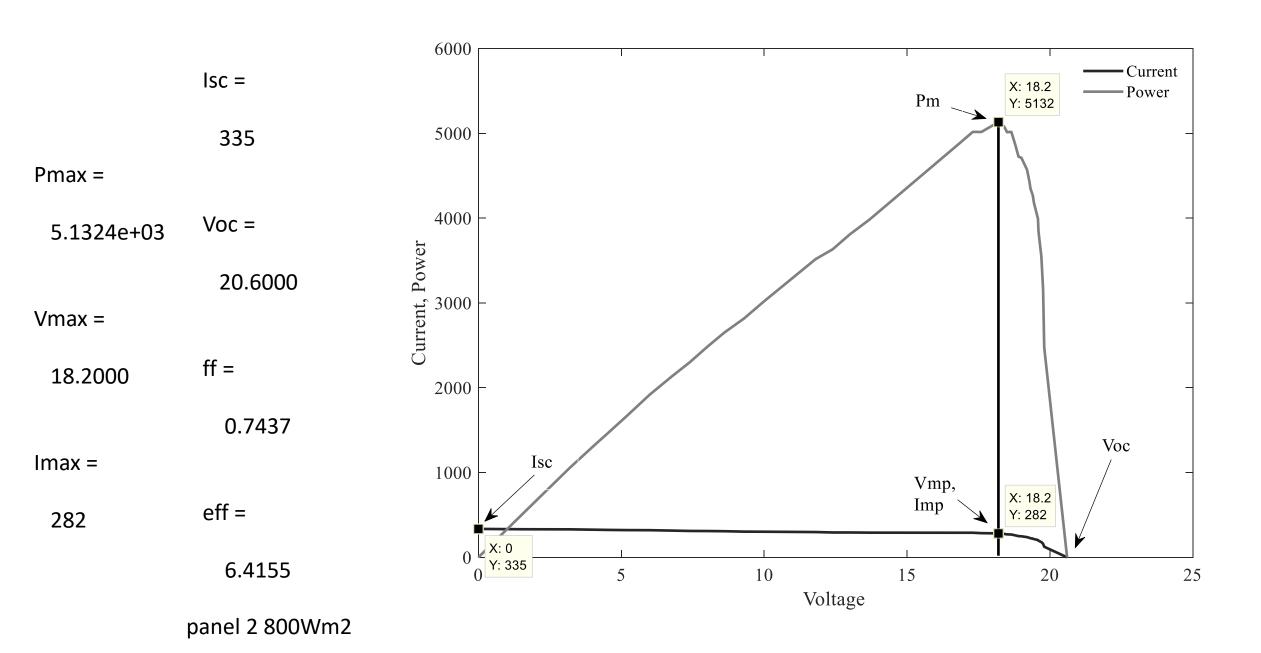


panel 1 800Wm2

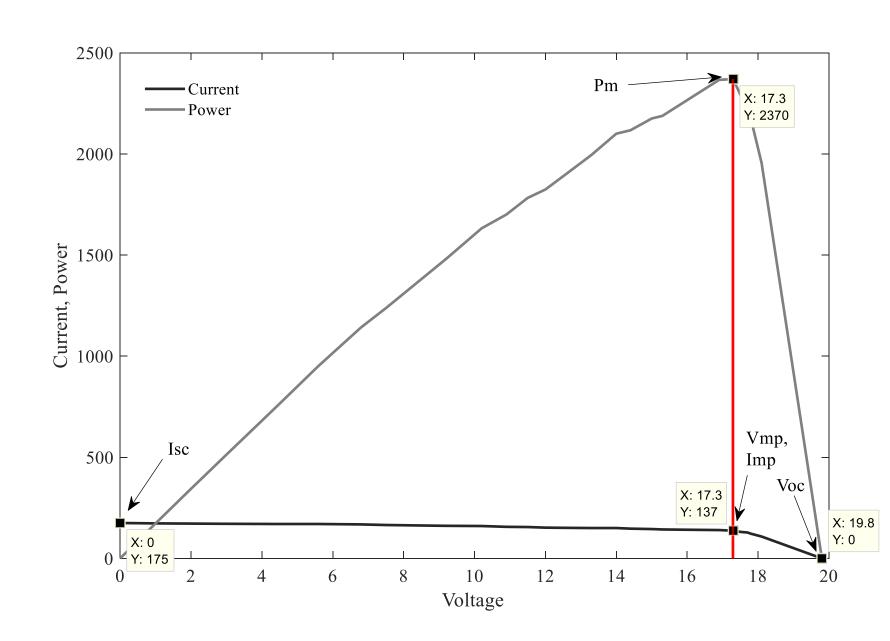




I-V Characteristics of Panel 02

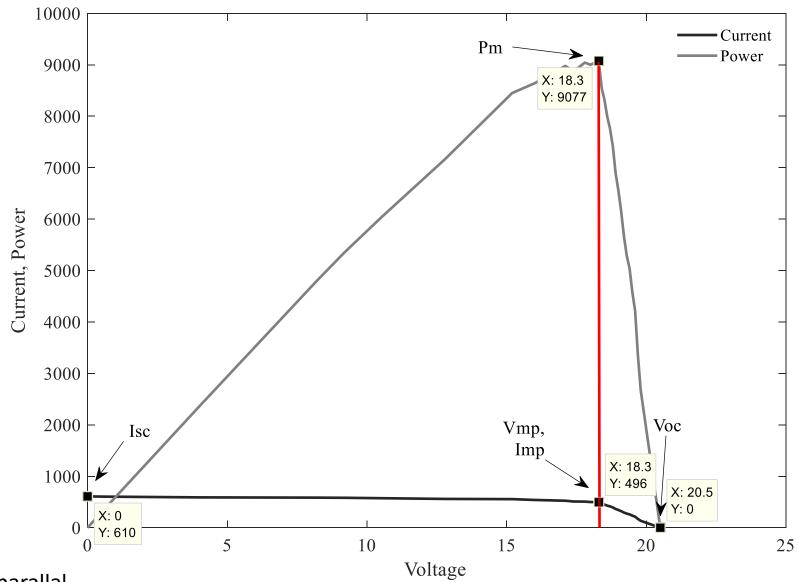


Isc =	Pmax =
175	2.3701e+03
Voc =	Vmax =
19.8000	17.3000
ff =	Imax = 137
0.6840	157
eff =	
5.9253	



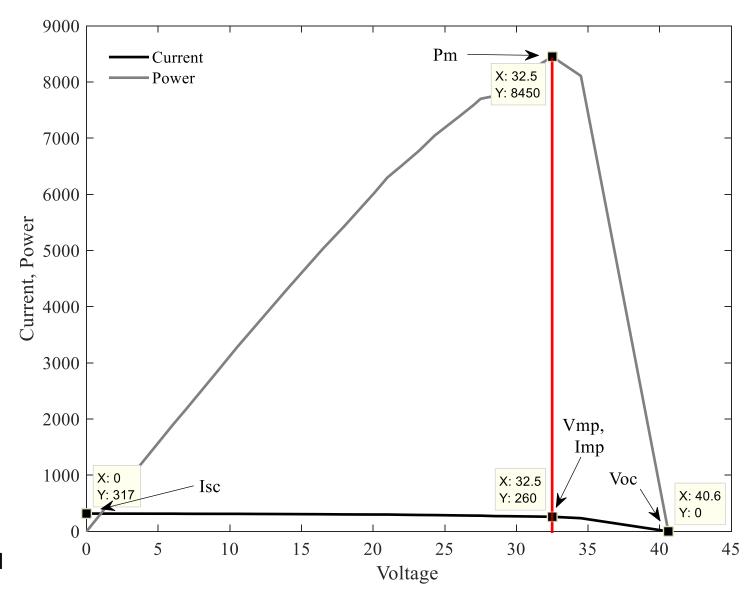
panel 2 400Wm2

Pmax =	Isc =
9.0768e+03	610
Vmax = 18.3000	Voc = 20.5000
Imax = 496.0000	ff = 0.7259
	eff = 11.3460



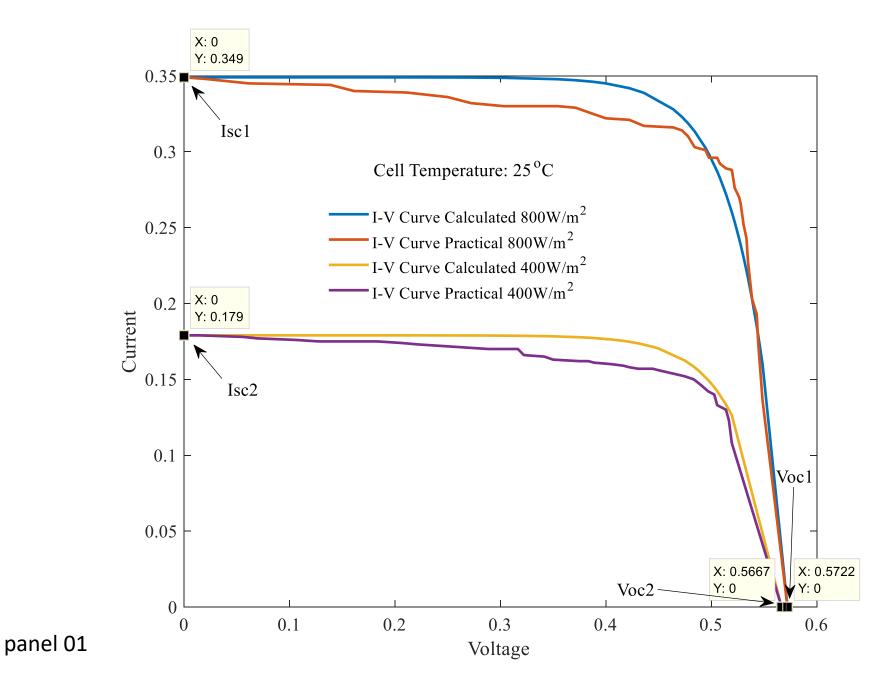
2 panel parallal 800Wm2

Isc =	Pmax =
317	8450
Voc =	Vmax =
40.6000	32.5000
ff = 0.6566	Imax = 260
eff =	
10.5625	

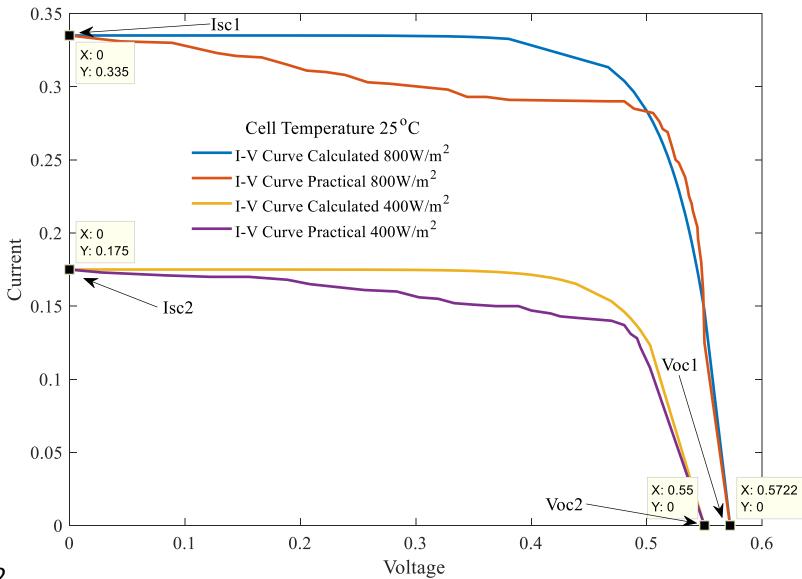


2 series panel 800Wm2

Ideality factor, n = 0.3236	Isc1 = 0.3490
	Voc1 = 0.5722
	Isc2 = 0.1790
	Voc2 = 0.5667

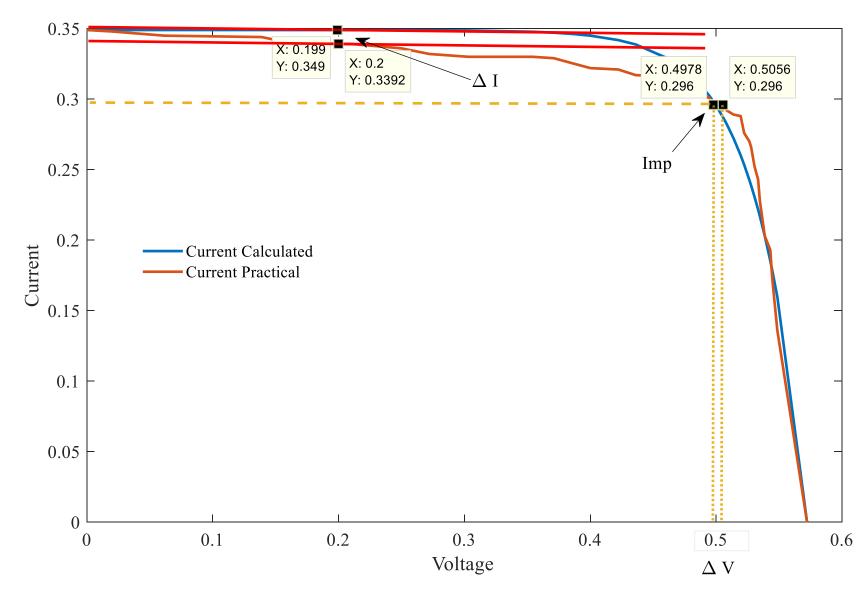


Ideality	Isc1 =
factor, n =	0.3350
1.3309	Voc1 = 0.5722
	Isc2 =
	0.1750
	Voc2 =
	0.5500



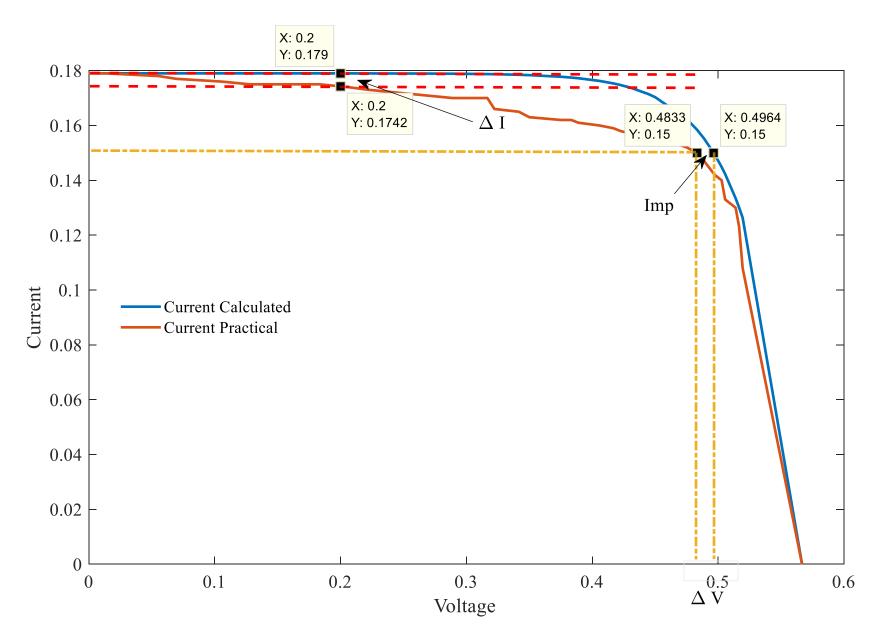
panel 02

Rs = Del V/Imp	Del I = Isc – I1
Del V= (0.5056- 0.4978)	V1/Ish = Rsh
	V1 = 0.2
Imp = 0.296	Rsh = 20.41
Rs = 0.026	



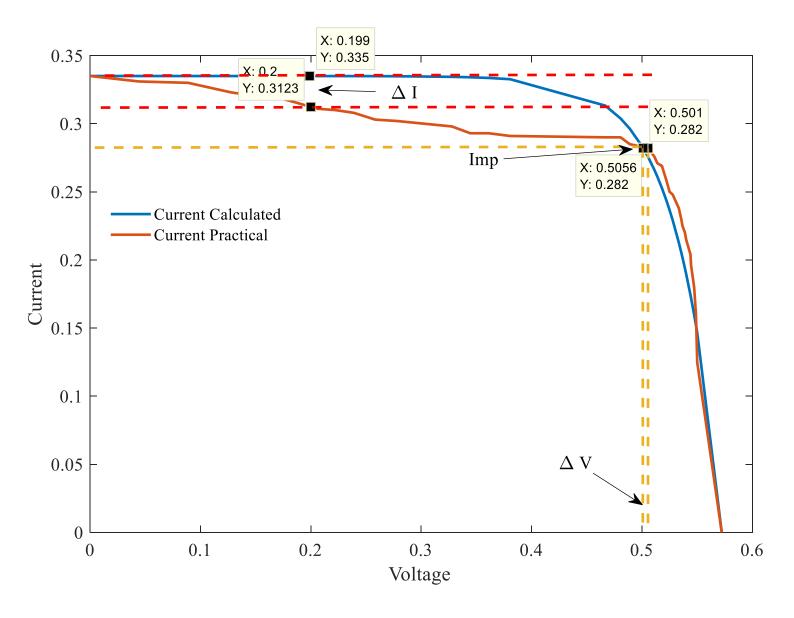
panel 01 800W/m2

Rs = Del V/Imp	Del I = Isc – I1 =Ish
Del V= 0.0131	V1/Ish = Rsh
Imp = 0.15	V1 = 0.2
Rs = 0.087	Rsh = 41.67



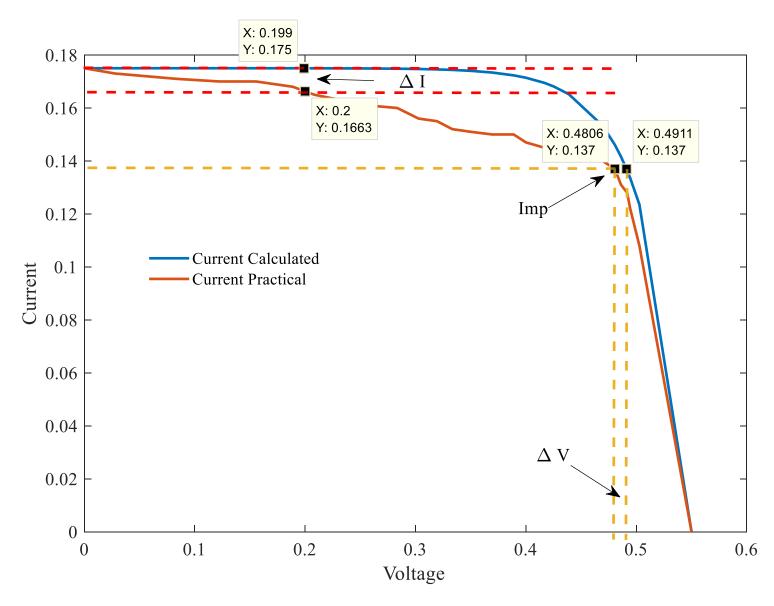
panel 01 400W/m2

Rs = Del V/Imp	Del I = Isc – I1 =Ish
Del V= 0.0046	V1/Ish = Rsh
Imp = 0.282	V1 = 0.2
Rs = 0.016	Rsh = 8.81



panel 02 800W/m2

Rs = Del V/Imp	Del I = Isc – I1 =Ish
Del V= 0.0105	   V1/Ish = Rsh
Imp = 0.137	V1 = 0.2
Rs = 0.077	Rsh = 22.99



panel 02 400W/m2